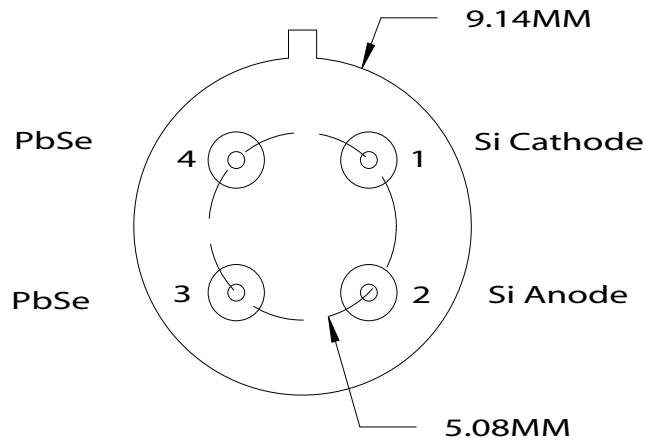


### Si SPECIFICATIONS

TOP Si PV PHOTODIODE  
 ACTIVE AREA - 3.5MM Dia  
 WAVELENGTH - .3-1.1u  
 SHUNT RESISTANCE - 1500M @10mV  
 DARK CURRENT - 0.2nA @10V  
 CAPACITANCE - 100pF @0V  
 RESPONSIVITY - .65A/W @900nm  
 NEP(W/Hz) - <math>1.3 \times 10^{-14}</math> @900nm  
 TIME CONSTANT - 2000ns @0V



### PbSe SPECIFICATIONS

BOTTOM PbSe PC DETECTOR  
 ACTIVE AREA - 2MMX2MM  
 WAVELENGTH - 1.0 - 4.7u  
 RESISTANCE - .3-1.5 M ohms  
 RESPONSIVITY - >3000V/W  
 $D^*(Pk,1000,1) \times 10^{-2.0}$   
 TIME CONSTANT - 3us

**NOTE:**

- All assemblies are hermetically sealed
- Custom filters are available
- Other active areas are available
- PbS and InGaAs materials are available

<b>DO NOT SCALE DRAWING</b>	DRAWN		DATE	<b>N.E.P.</b> NEW ENGLAND PHOTOCONDUCTOR				
	CHECKED		DATE					
	DESIGNER	GG	DATE	<b>FS-2/2.5-5</b>				
	ENGINEER	PB	DATE					
MATERIAL:	PROJECT ENGINEER		DATE					
FINISH SPECS:	PROJECT APPROVAL		DATE	SIZE	CODE IDENT. NO.	TYPE	1489	REV
	PMB 3/3/09			A				
				SCALE	none		SHEET	1